

# Irradiation of EUV-mirrors with multiple FEL pulses below the single shot damage threshold

Igor Makhotkin (1), Hartmut Enkisch (2), Ryszard Sobierajski (3), Jaromir Chalupský (4), Kai Tiedtke (5), Gosse de Vries (6), Michael Störmer (7), Frank Scholze (8), Frank Siewert (9); Robbert van de Kruijs (1), Igor Milov (1), Eric Louis (1), Ivanna Yatsyna (3), Marek Jurek (3), Libor Juha (4), Věra Hájková (4), Vojtěch Vozda (4), Tomáš Burian (4), Karel Saksl (4), Bart Faatz (5), Barbara Keitel (5), Elke Ploenjes (5), Siegfried Schreiber (5), Sven Toleikis (5), Rolf Loch (5), Martin Hermann (2), Sebastian Strobel (2), Han-Kwang Nienhuys (6)

- 1) MESA+ Institute for Nanotechnology, University of Twente, Drienerlolaan 5, 7522 NB Enschede, The Netherlands
- 2) Carl Zeiss SMT GmbH, Rudolf-Eber-Strasse 2, 73447 Oberkochen, Deutschland
- 3) Institute of Physics, Polish Academy of Sciences, Al. Lotników 32/46, PL-02-668 Warsaw, Poland
- 4) Institute of Physics, Academy of Sciences of the Czech Republic, Na Slovance 2, 182 21 Prague 8, Czech Republic
- 5) Deutsches Elektronen-Synchrotron DESY, Notkestrasse 85, 22607 Hamburg, Germany
- 6) ASML Netherlands B.V., P.O. Box 324, 5500 AH Veldhoven, The Netherlands
- 7) Helmholtz-Zentrum Geesthacht, Max-Planck-Strasse 1, 21502 Geesthacht, Germany
- 8) Physikalisch-Technische Bundesanstalt, Abbestr. 2-12, 10587 Berlin, Germany
- 9) Helmholtz Zentrum Berlin, Elektronenspeicherring BESSY-II, Institut für Nanometer Optik und Technologie, Albert-Einstein-Str. 15, 12489 Berlin, Germany

A free-electron laser (FEL) is an intense sources of near monochromatic light. The FEL principle is mentioned as source for lithography. As FEL output comes in ultra-short pulses, optics and coatings are needed that withstand short, and intense light pulses. It was shown that a single light pulse of 13.5 nm wavelength does not damage typical reflective coatings until extremely high pulse energies per unit irradiated area. Critical single shot damage threshold (SSDT) levels have been reported to be 45 mJ/cm<sup>2</sup> for normal incidence reflective Mo/Si multilayer coatings (Ref. 1) and 80 mJ/cm<sup>2</sup> at 4° grazing incidence for amorphous carbon (Ref. 2). In practice, in a lithography application optics are subject to large number of pulses. (Ref. 3). This paper/poster describes experimental determination of the multi shot damage threshold (MSDT) of grazing and normal incidence EUV coatings for 13.5 nm wavelength. The experiments have been executed at the Free-electron LASer in Hamburg (FLASH). The exposures were performed for various fluence rates up to 10 % of SSDT values for corresponding materials and for various number of pulses up to 16M. After exposures the change of reflectivity of 13.5 nm EUV light was measured in exposed spots. The measurements showed that reflectivity of coatings exposed to 10% of SSDT 16M pulses was slightly changed. These small observed changes are ascribed to non-optimum vacuum conditions of the experiment resulting in EUV induced surface modifications.

## References

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